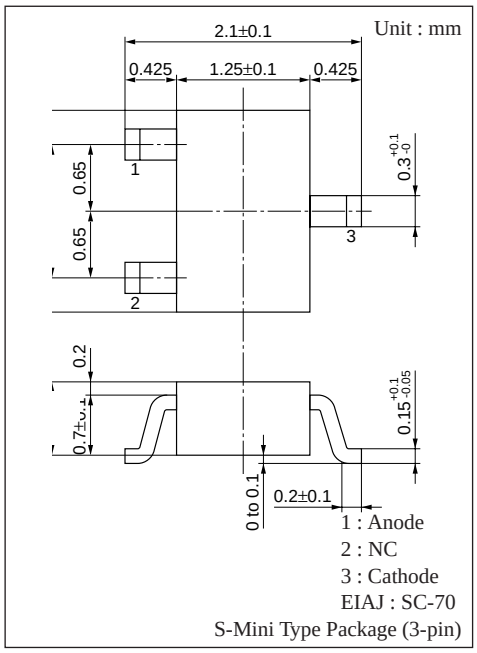
MA3Z551

Silicon epitaxial planer type

For attenuation of high-frequency variable resistor

■ Features

- Small diode capacity C_D
- Large variable range of forward dynamic resistance r_f
- Mini package, enabling down-sizing of the equipment and automatic insertion through taping and magazine package

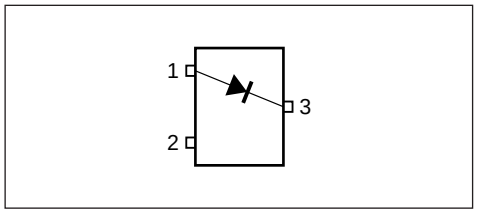


Marking Symbol : MY

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	45	V
Forward current (DC)	I_F	100	mA
Power dissipation	P_D	150	mW
Operating ambient temperature	T_{opr}	– 25 to + 85	˚C
Storage temperature	T_{stg}	– 55 to +150	˚C

■ Internal Connection



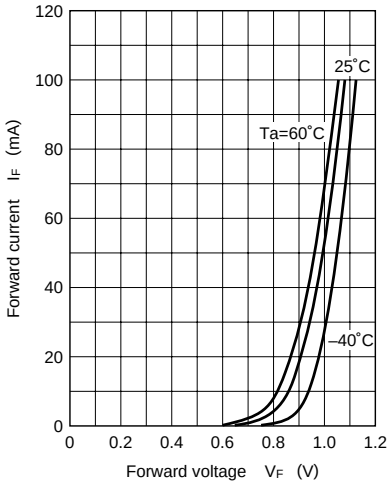
■ Electrical Characteristics (Ta= 25˚C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 40V			100	nA
Forward voltage (DC)	V_F	I_F=100mA		1.05	1.2	V
Diode capacitance	C_D	V_R=15V, f=1MHz		0.3	0.5	pF
Forward dynamic resistance	r_{f1} *	I_F=10μA, f=100MHz	1	2		kΩ
	r_{f2} *	I_F=10mA, f=100MHz		6	10	Ω

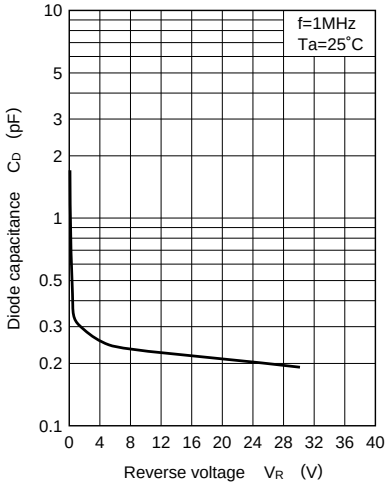
Note 1. Rated input/output frequency : 100MHz
2. * r_f measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

■ Marking

$I_F - V_F$



$C_D - V_R$



$I_R - Ta$